

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT			ATTY DOCKET NO. 536-009.13		SERIAL NO. 10/520396 To be assigned		
			APPLICANT: Hans Joachim Müssig				
			FILING DATE: Herewith 1/4/05		ART UNIT: To be assigned 2813		
UNITED STATES PATENT DOCUMENTS							
EXAM. INITIAL		DOCUMENT NUMBER	ISSUE/PUBL DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MDH	US	2002/0036313	3-28-2002	Sam Yang et al.	—	—	—
	US	2003/0228747	12-11-2003	Kie Y. Ahn et al.	—	—	—
	US	6,656,852	12-2-2003	Antonio Luis Pacheco Rotondaro et al.	—	—	—
	US	2003/0119291	6-26-2003	Kie Y. Ahn	—	—	—
	US	5,356,833	10-18-1994	Papu D. Maniar et al.	—	—	—
↓	US	2003/0193061	10-16-2003	Hans-Jörg Osten	—	—	—
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	TRANSLATION YES/NO
MDH	WO	02/097895	12-5-2002	Dietmar Krüger et al.	—	—	abstract only
OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)							
MDH		Surface Science 504 (2002) 159-166, XP-001189099, Initial stages of praseodymium oxide film formation on Si(001), H.-J. Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany; received 8 September 2001, accepted for publication 3 Dec. 2001.					
MDH		2001 IRW Final Report, O-7803-7167-4/01/2001 IEEE, Can Praseodymium Oxide be an Alternative High-K Gate Dielectric Material for Silicon Integrated Circuits?, H. -J Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany.					
Examiner <i>Monica D. Ransom</i>				Date: <i>August 24, 2005</i>			